







## **High Power next Core (HPnC)**

## **FEATURES**

- Latest chip technology (X-series and SiC-SBD)
  - > Available with Fuji X-series IGBT and FWD
  - > Also available with Fuji SiC FWD
- High reliability
  - > CTI>600 for higher anti-tracking
  - High thermal cycling capability with ultrasonic welded terminals and MgSiC base plate
  - Improvement of delta Tj power cycle capability by using 7G Package technology
  - ▶ Tj operation target is 175 °C

- RoHS compliance
  - > RoHS solder
  - Ultrasonic welded terminals
- Over temperature protection
  - > Thermal sensor installed

Line-up Plan			
Technology		Rated Voltage	Chip IGBT / FWD
	Silicon	1700 V	1000 A
	(IGBT/Si-Diode)	3300 V	450 A
	Hybrid	1700 V	1000 A
	(IGBT/SiC-SBD)	3300 V	450 A



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